



### 5.0V, 4.9 GHz TO 5.85 GHz POWER AMPLIFIER

#### Package: Laminate Package, 10-pin, 4mm x 4mm x 0.975mm



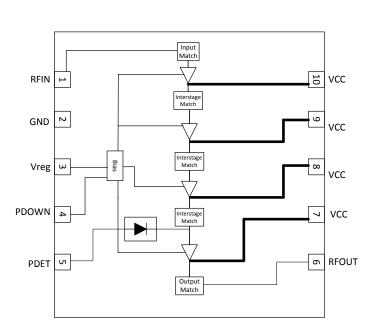
**RF5626** 

### **Features**

- Single Voltage: 5.0V
- 24.5dBm Linear Output Power
- 50Ω Input and Output
- High Gain 32dB typical

### **Applications**

- WLAN 11a/n
- Commercial and Consumer Systems



**Functional Block Diagram** 

### **Product Description**

Proposed

The RF5626 is a fully integrated MMIC which is in a 4mm x 4mm laminate package. This fully integrated MMIC is intently specified to address the general market for high power, high band (4.9GHz to 5.85GHz) 802.11a/n WLAN systems. The RF5626 is a WLAN MMIC PA with integrated detector and integrated input/ouput match to  $50\Omega$ .

### **Ordering Information**

RF5626 **Power Amplifier** RF5626PCKA-410 Fully Assembled Evaluation Board

### **Optimum Technology Matching® Applied**

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# RF5626

### Proposed



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#### **Absolute Maximum Ratings**

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Parameter	Rating	Unit
Supply Voltage (RF Applied)	-0.5 to +5.25	V
Supply Voltage (No RF Applied)	-0.5 to +6.0	V
DC Supply Current	TBD	mA
Input RF Power with 50 $\Omega$ Output Load	TBD	dBm
Input RF Power with Non-50 $\Omega$ Output Load	TBD	dBm
Operating Ambient Temperature	-30 to +85	°C
Storage Temperature	-40 to +150	°C

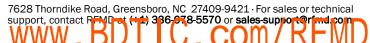
Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

RoHS status based on EUDirective2002/95/EC (at time of this document revision).

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Parameter	Specification		Unit	Condition		
Farameter	Min.	Тур.	Max.	Unit	Condition	
Typical Conditions					T=25 °C, V <sub>CC</sub> =5.0V, V <sub>REG</sub> =3.0V, P <sub>DOWN</sub> =3.0V, using a standard IEEE802.11a waveform at 54Mbps, 64 QAM, unless other- wise noted.	
Frequency	4900		5150	MHz	De-rated performance	
	5150		5850	MHz		
Output Power		24.5		dBm	V <sub>CC</sub> =5.0V, V <sub>REG</sub> =ON	
EVM		3		%	At rated P <sub>OUT</sub> , V <sub>CC</sub> =5V	
Gain		32		dB	At rated P <sub>OUT</sub> , 11a modulation	
Gain Variation			2.5	dB		
Power Supply						
V <sub>CC</sub>		5		V		
Quiescent Current		500		mA	At V <sub>CC</sub> =5V	
Operation Current		600		mA	At V <sub>CC</sub> =5V, 11a modulation	
Leakage		100		μΑ	At $V_{CC}$ =5V, $V_{REG}$ =0.2V	
V <sub>REG</sub>		3.0		V		
Input Return Loss		15		dB		
Second Harmonic (F <sub>C</sub> =5.3GHz to 5.85GHz			-43	dBm	At rated P <sub>OUT</sub> , measured in 1MHz RSB	







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RF	56	26

Pin	Function	Description
1	RFIN	RF input port - DC blocked and 50 $\Omega$ internally matched.
2	GND	Ground connection.
3	VREG	Bias control pin - requires a regulated supply to maintain nominal bias current.
4	PDOWN	Power down pin - apply <0.6VDC to power down the power amplifier stages; apply 1.75VDC to 5.0VDC to power up. If function is not desired, pin may be connected to VREG
5	PDET	Power detector pin - provides an output voltage proportional to the RF output power level.
6	RFOUT	RF output port - 50 $\Omega$ internally matched.
7	VCC	Amplifier supply voltage.
8	VCC	Amplifier supply voltage.
9	VCC	Amplifier supply voltage.
10	VCC	Amplifier supply voltage.
Pkg Base	GND	Ground connection - the backside of the package should be connected to the ground plane through as short a connection as possible (e.g.: PCB vias under the device.)





## Proposed



**Pin Out** 10 VCC RFIN ⊢ Ν 9 GND vcc Vreg ω 00 VCC 4 NWOD9 7 VCC RFOUT 6 ы PDET

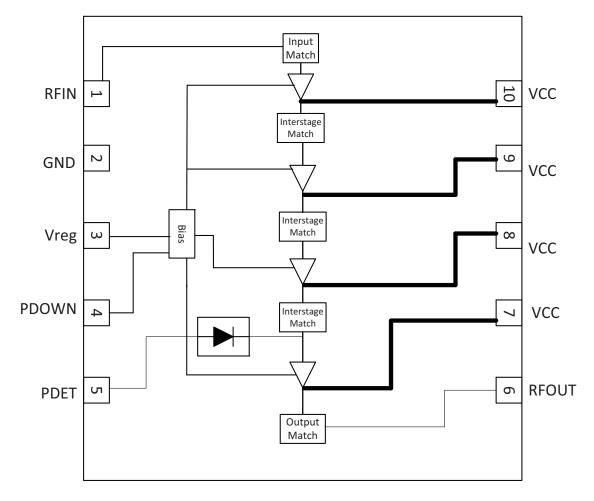










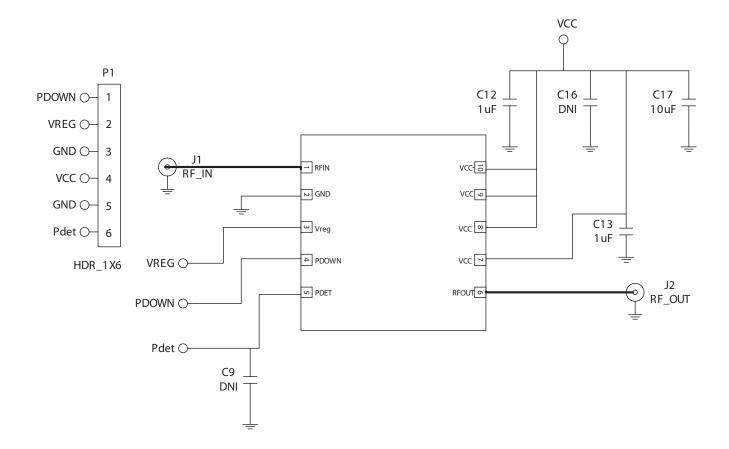


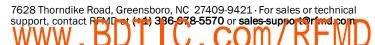


### Proposed



### **Evaluation Board Layout**

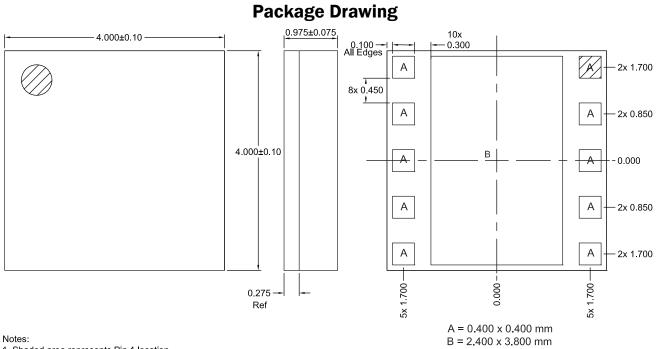












1. Shaded area represents Pin 1 location









### **PCB** Design Requirements

#### **PCB Surface Finish**

The PCB surface finish used for RFMD's qualification process is electroless nickel, immersion gold. Typical thickness is 3 µinch to 8µinch gold over 180µinch nickel.

#### **PCB Land Pattern Recommendation**

PCB land patterns for RFMD components are based on IPC-7351 standards and RFMD empirical data. The pad pattern shown has been developed and tested for optimized assembly at RFMD. The PCB land pattern has been developed to accommodate lead and package tolerances. Since surface mount processes vary from company to company, careful process development is recommended.

#### PCB Metal Land and Solder Mask Pattern

